00684.003160 PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	:	Examiner: K. Brown
Yoshinori MIWA et al.	)	
	:	Group Art Unit: 2851
Application No.: 09/819,671	)	
	:	
Filed: March 29, 2001	)	
	:	
For: EXPOSURE APPARATUS AND DEVICE MANUFACTURING METHOD	)	October 23, 2002

The Commissioner for Patents
Washington, D.C. 20231

AMENDMENT WITH PETITION FOR EXTENSION OF TIME

Sir:

Applicants petition the Commissioner for Patents to extend the time for response to the Office Action dated May 23, 2002, for two months from August 23, 2002, to October 23, 2002. A check in the amount of $400.00 for payment of the extension fee is enclosed. Please charge any additional fee required for the extension, or credit any overpayment, to Deposit Account 06-1205.

In response to the Official Action dated May 23, 2002, please amend the above-identified application as follows:

IN THE ABSTRACT

Please cancel the current abstract and insert the following. A marked-up copy showing the changes made to the abstract is attached hereto in Appendix A.

-- An exposure apparatus to be used with an excimer laser as a light source includes an optical system disposed along a path of excimer laser light, a chamber for accommodating the optical system therein and having an inside space being able to be replaced by a predetermined gas, a gas circulation mechanism having a gas circulation path for connecting a gas discharging port for discharging a gas from the chamber and a gas supplying port for supplying a gas into the chamber, and a switching device for selectively using plural purifiers disposed in the gas circulation path. --

IN THE SPECIFICATION:

Please amend the specification as follows:

Please substitute the paragraph beginning at page 1, line 12, with the following. A marked-up copy of this paragraph, showing the changes made thereto, is attached in Appendix A.

-- In projection exposure apparatus for the manufacture of semiconductor integrated circuits, light of various wavelength regions is projected to a substrate as an exposure beam. As regards the exposure beam, for example, g-line (436 nm), i-line (365 nm), a KrF excimer laser (248 nm) or an ArF excimer laser (193 nm) is used. --